Abstracts

Consistent small-signal and RF-noise parameter modelling of carbon doped InP/InGaAs HBT

M. Agethen, S. Schuller, P. Velling, W. Brockerhoff and F.-J. Tegude. "Consistent small-signal and RF-noise parameter modelling of carbon doped InP/InGaAs HBT." 2001 MTT-S International Microwave Symposium Digest 01.3 (2001 Vol. III [MWSYM]): 1765-1768 vol.3.

In this work a consistent small-signal and rf-noise parameter model of InP/InGaAs HBT is presented. This model is based on the typical three-mesa design of HBT and correlates intrinsic noise sources to specific device regions. Bias dependent investigation of S- and RF-noise parameters proves the consistency of the model.

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